

## SI6968BEDQ-T1-GE3-VB Datasheet

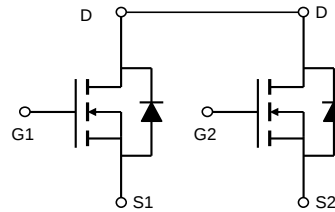
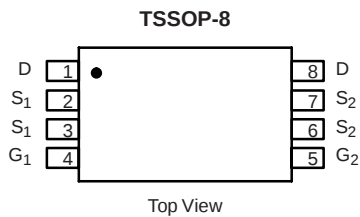
## Dual N-Channel MOSFET

**PRODUCT SUMMARY**

| $V_{DS}$ (V) | $R_{DS(on)}$ ( $\Omega$ ) | $I_D$ (A) |
|--------------|---------------------------|-----------|
| 20           | 0.014 at $V_{GS} = 4.5$ V | 7.6       |
|              | 0.018 at $V_{GS} = 2.5$ V | 6.5       |

**FEATURES**

- Halogen-free Option Available
- Trench Power MOSFETs


**RoHS\***  
 COMPLIANT
**ABSOLUTE MAXIMUM RATINGS**  $T_A = 25^\circ\text{C}$ , unless otherwise noted

| Parameter                                                           | Symbol         | 10 s        | Steady State | Unit             |
|---------------------------------------------------------------------|----------------|-------------|--------------|------------------|
| Drain-Source Voltage                                                | $V_{DS}$       | 20          |              | V                |
| Gate-Source Voltage                                                 | $V_{GS}$       | $\pm 12$    |              |                  |
| Continuous Drain Current ( $T_J = 150^\circ\text{C}$ ) <sup>a</sup> | $I_D$          | 7.6         | 6.2          | A                |
|                                                                     |                | 6.5         | 4.5          |                  |
| Pulsed Drain Current                                                | $I_{DM}$       | 30          |              |                  |
| Continuous Source Current (Diode Conduction) <sup>a</sup>           | $I_S$          | 1.5         | 1.0          |                  |
| Maximum Power Dissipation <sup>a</sup>                              | $P_D$          | 1.5         | 1.0          | W                |
|                                                                     |                | 0.96        | 0.64         |                  |
| Operating Junction and Storage Temperature Range                    | $T_J, T_{stg}$ | - 55 to 150 |              | $^\circ\text{C}$ |

**THERMAL RESISTANCE RATINGS**

| Parameter                                | Symbol     | Typ. | Max. | Unit               |
|------------------------------------------|------------|------|------|--------------------|
| Maximum Junction-to-Ambient <sup>a</sup> | $R_{thJA}$ | 72   | 83   | $^\circ\text{C/W}$ |
|                                          |            | 100  | 120  |                    |
| Maximum Junction-to-Foot (Drain)         | $R_{thJF}$ | 55   | 70   |                    |

Notes:

a. Surface Mounted on FR4 board,  $t \leq 10$  s.

\* Pb containing terminations are not RoHS compliant, exemptions may apply.

**SPECIFICATIONS**  $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted

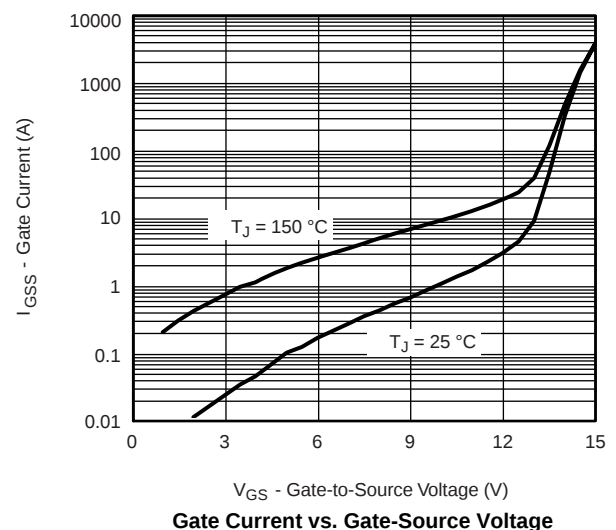
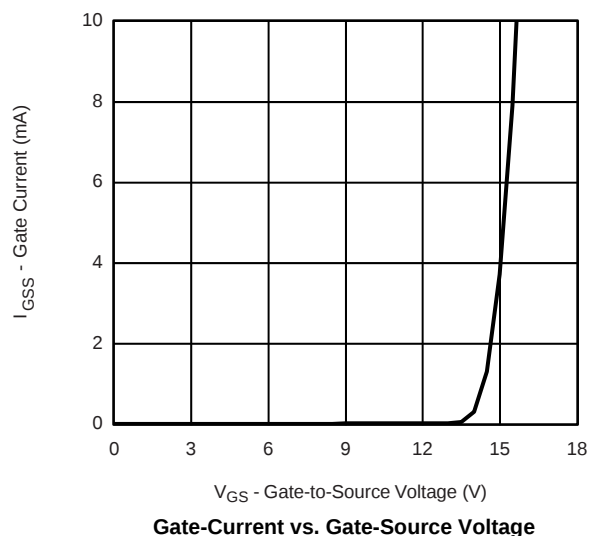
| Parameter                                     | Symbol       | Test Conditions                                                                                                                  | Min. | Typ. <sup>a</sup> | Max.      | Unit          |
|-----------------------------------------------|--------------|----------------------------------------------------------------------------------------------------------------------------------|------|-------------------|-----------|---------------|
| <b>Static</b>                                 |              |                                                                                                                                  |      |                   |           |               |
| Gate Threshold Voltage                        | $V_{GS(th)}$ | $V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$                                                                               | 0.6  |                   | 1.6       | V             |
| Gate-Body Leakage                             | $I_{GSS}$    | $V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 4.5\text{ V}$                                                                              |      |                   | $\pm 200$ | nA            |
| Zero Gate Voltage Drain Current               | $I_{DSS}$    | $V_{DS} = 20\text{ V}$ , $V_{GS} = 0\text{ V}$                                                                                   |      |                   | 1         | $\mu\text{A}$ |
|                                               |              | $V_{DS} = 20\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 70\text{ }^{\circ}\text{C}$                                              |      |                   | 25        |               |
| On-State Drain Current <sup>b</sup>           | $I_{D(on)}$  | $V_{DS} \leq 5\text{ V}$ , $V_{GS} = 4.5\text{ V}$                                                                               | 30   |                   |           | A             |
| Drain-Source On-State Resistance <sup>b</sup> | $R_{DS(on)}$ | $V_{GS} = 4.5\text{ V}$ , $I_D = 6.5\text{ A}$                                                                                   |      | 0.014             |           | $\Omega$      |
|                                               |              | $V_{GS} = 2.5\text{ V}$ , $I_D = 5.5\text{ A}$                                                                                   |      | 0.018             |           |               |
| Forward Transconductance <sup>b</sup>         | $g_{fs}$     | $V_{DS} = 10\text{ V}$ , $I_D = 6.5\text{ A}$                                                                                    |      | 30                |           | S             |
| Diode Forward Voltage <sup>b</sup>            | $V_{SD}$     | $I_S = 1.5\text{ A}$ , $V_{GS} = 0\text{ V}$                                                                                     |      | 0.71              | 1.2       | V             |
| <b>Dynamic<sup>a</sup></b>                    |              |                                                                                                                                  |      |                   |           |               |
| Total Gate Charge                             | $Q_g$        | $V_{DS} = 10\text{ V}$ , $V_{GS} = 4.5\text{ V}$ , $I_D = 6.5\text{ A}$                                                          |      | 12                | 18        | nC            |
| Gate-Source Charge                            | $Q_{gs}$     |                                                                                                                                  |      | 2.2               |           |               |
| Gate-Drain Charge                             | $Q_{gd}$     |                                                                                                                                  |      | 3.6               |           |               |
| Turn-On Delay Time                            | $t_{d(on)}$  | $V_{DD} = 10\text{ V}$ , $R_L = 10\text{ }\Omega$<br>$I_D \cong 1\text{ A}$ , $V_{GEN} = 4.5\text{ V}$ , $R_G = 6\text{ }\Omega$ |      | 245               | 365       | ns            |
| Rise Time                                     | $t_r$        |                                                                                                                                  |      | 330               | 495       |               |
| Turn-Off Delay Time                           | $t_{d(off)}$ |                                                                                                                                  |      | 860               | 1300      |               |
| Fall Time                                     | $t_f$        |                                                                                                                                  |      | 510               | 765       |               |

Notes:

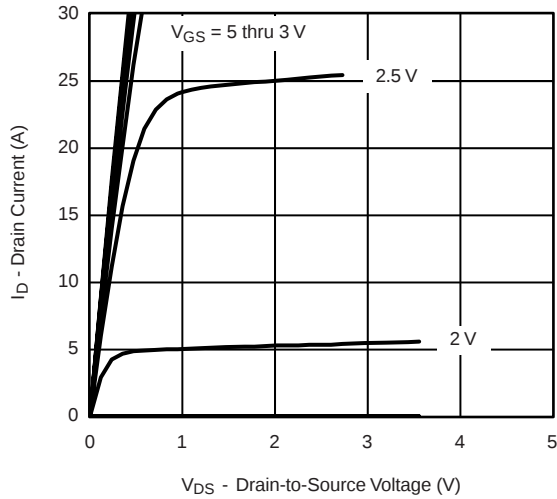
a. For design aid only; not subject to production testing.

b. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

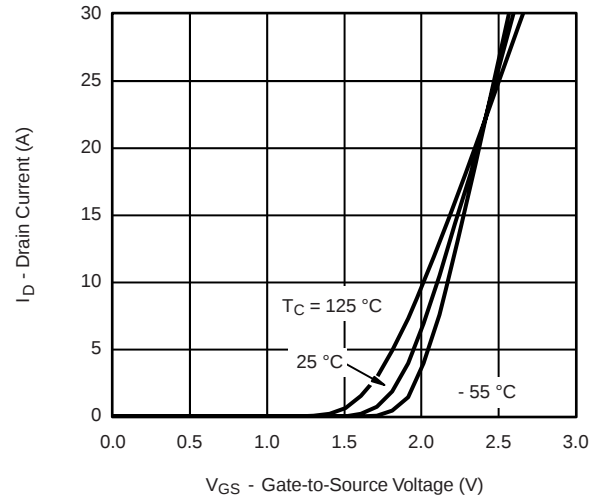
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS**  $25\text{ }^{\circ}\text{C}$ , unless otherwise noted

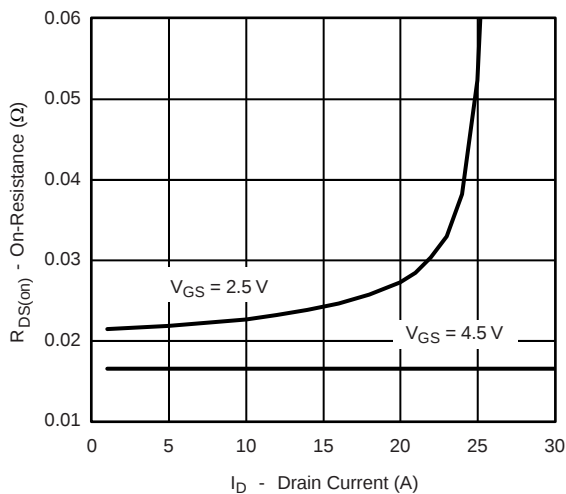
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



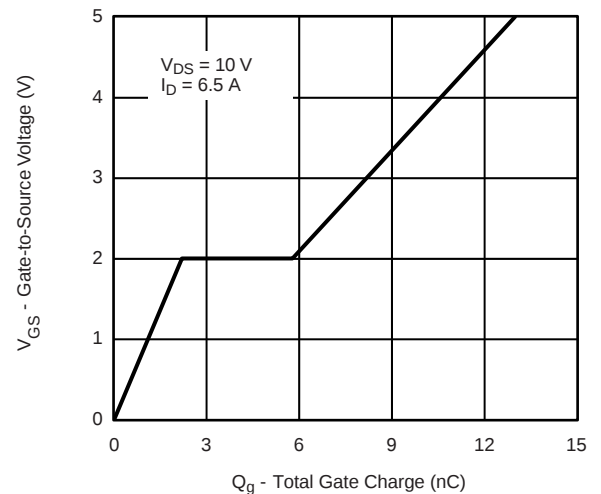
Output Characteristics



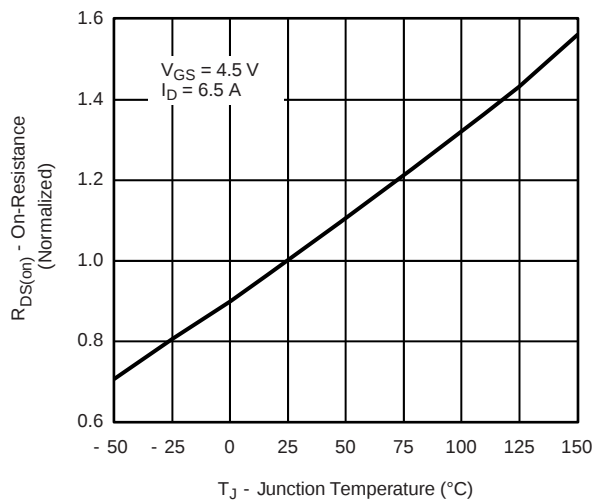
Transfer Characteristics



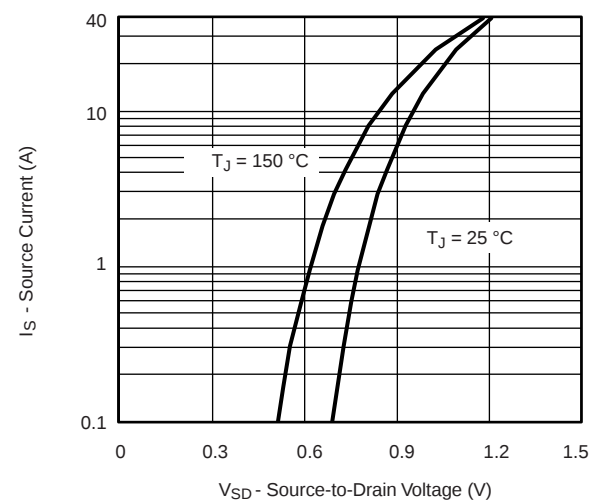
On-Resistance vs. Drain Current



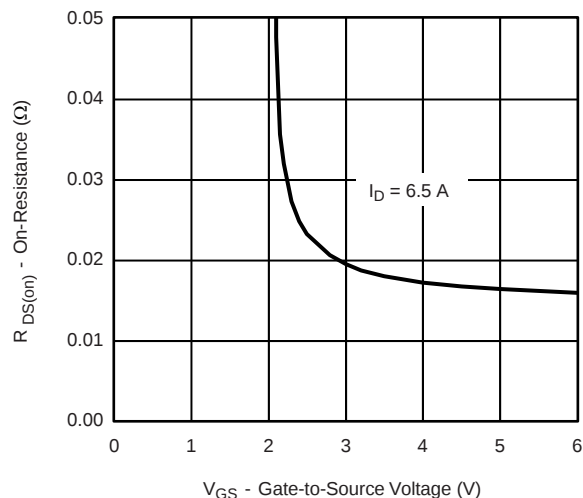
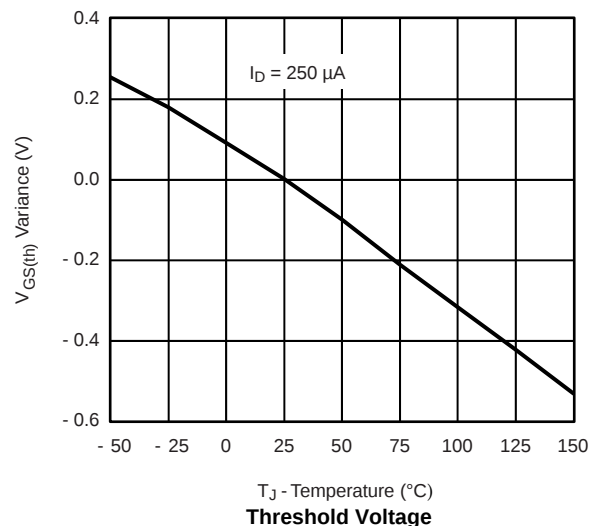
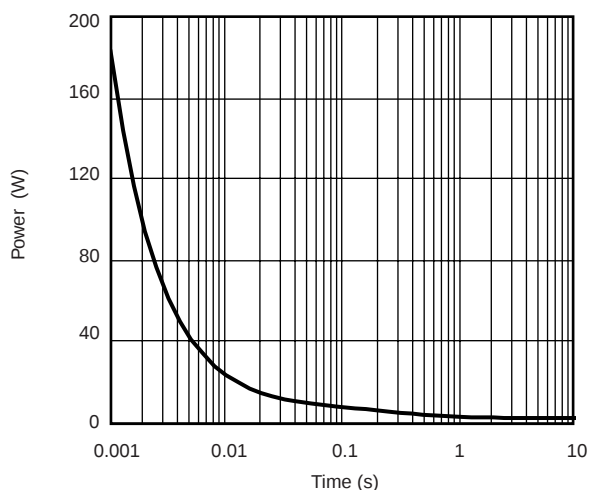
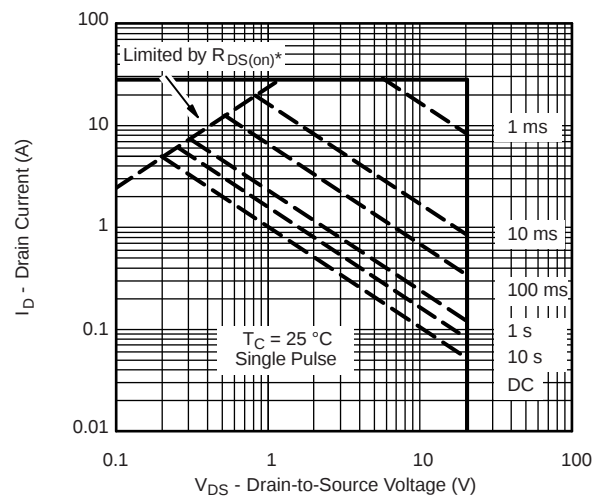
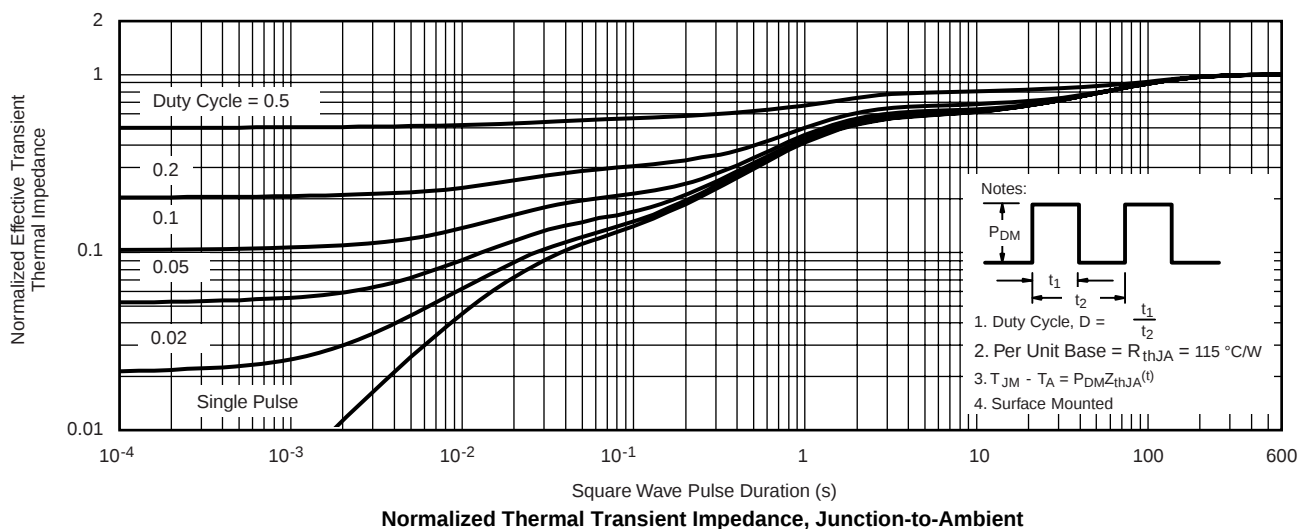
Gate Charge



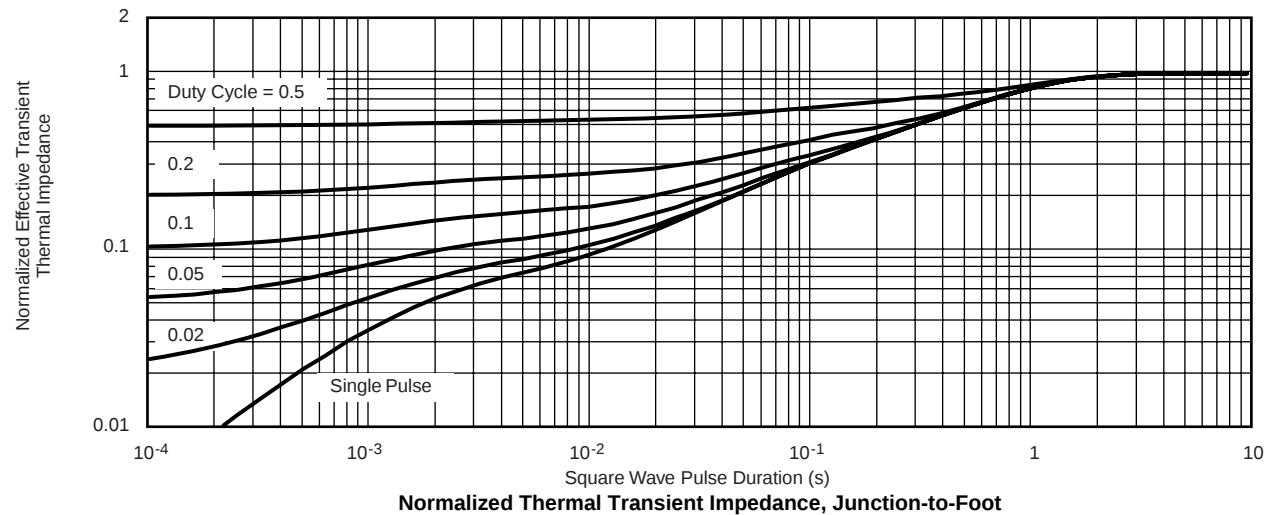
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

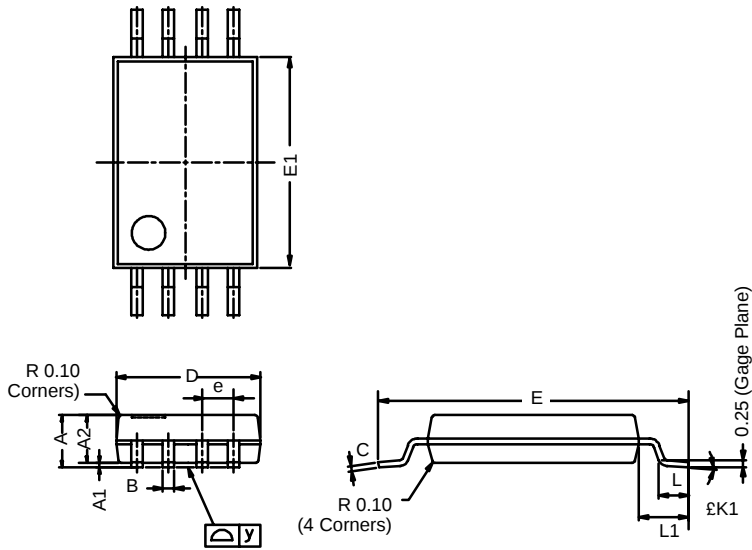
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted

**On-Resistance vs. Gate-to-Source Voltage**

**Threshold Voltage**

**Single Pulse Power**

**Safe Operating Area, Junction-to-Case**


**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**TSSOP: 8-LEAD**

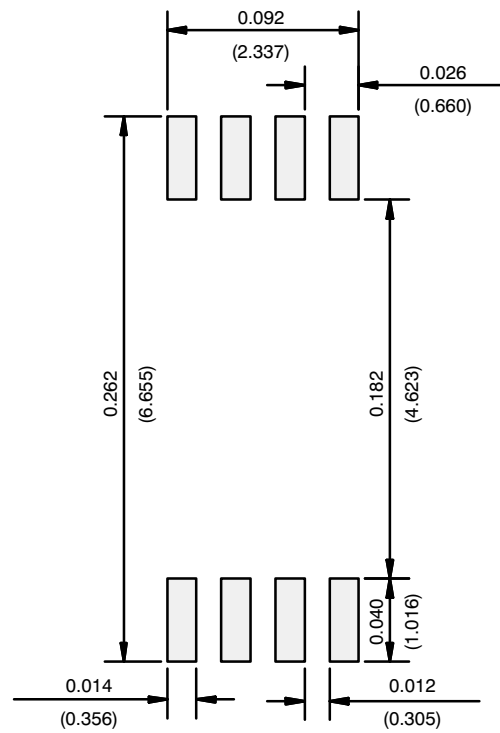
JEDEC Part Number: MO-153



| Dim            | MILLIMETERS |       |      |
|----------------|-------------|-------|------|
|                | Min         | Nom   | Max  |
| A              | —           | —     | 1.20 |
| A <sub>1</sub> | 0.05        | 0.10  | 0.15 |
| A <sub>2</sub> | 0.80        | 1.00  | 1.05 |
| B              | 0.19        | 0.28  | 0.30 |
| C              | —           | 0.127 | —    |
| D              | 2.90        | 3.00  | 3.10 |
| E              | 6.20        | 6.40  | 6.60 |
| E <sub>1</sub> | 4.30        | 4.40  | 4.50 |
| e              | —           | 0.65  | —    |
| L              | 0.45        | 0.60  | 0.75 |
| L <sub>1</sub> | 0.90        | 1.00  | 1.10 |
| Y              | —           | —     | 0.10 |
| £K1            | 0°          | 3°    | 6°   |

ECN: S-03946—Rev. G, 09-Jul-01  
DWG: 5844

## RECOMMENDED MINIMUM PADS FOR TSSOP-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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